

Abstract of the Disclosure:

The power semiconductor element has an emitter region and a stop zone in front of the emitter region. The conductivities of the emitter region and of the stop zone are opposed to one another. In order to reduce not only the static but also the dynamic loss of the power semiconductor foreign atoms are used in the stop-zone. The foreign atoms have at least one energy level within the band gap of the semiconductor and at least 200 meV away from the conduction band and valence band of the semiconductor.

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